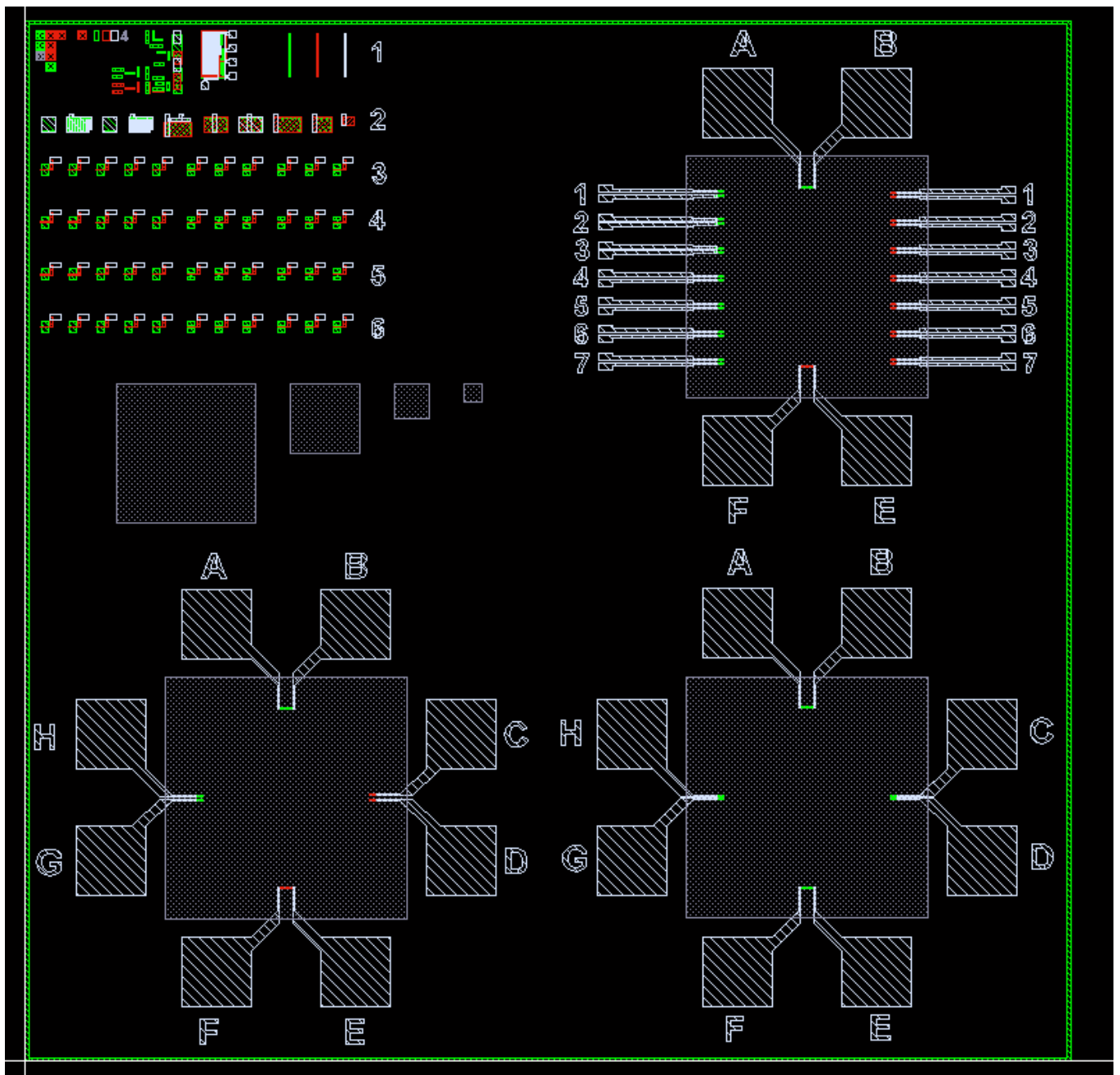
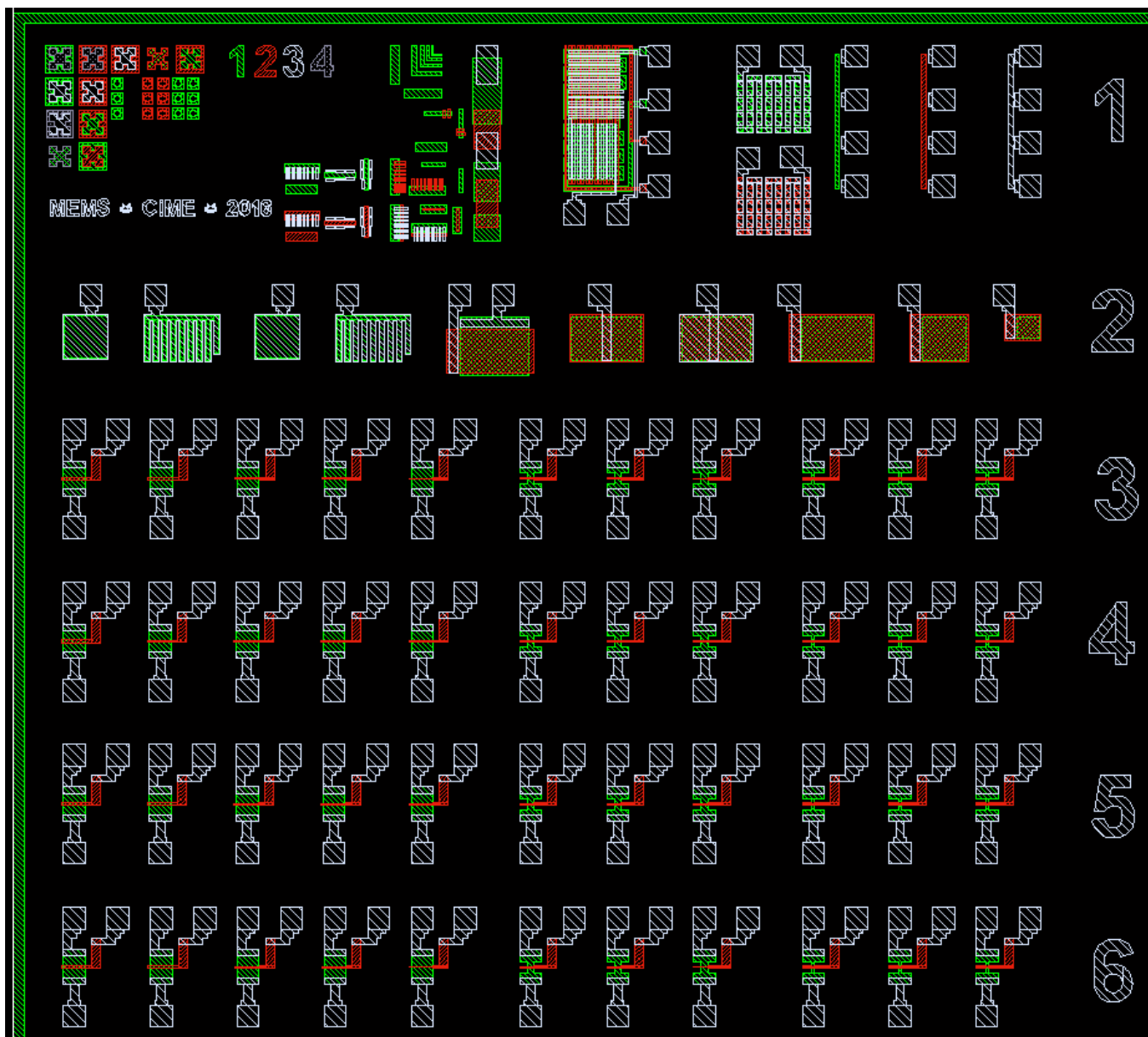


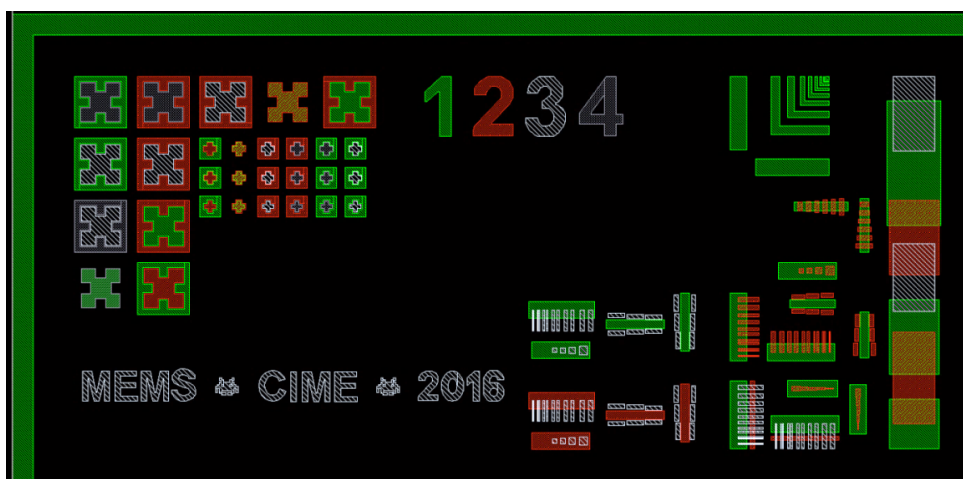
**Réticule :**



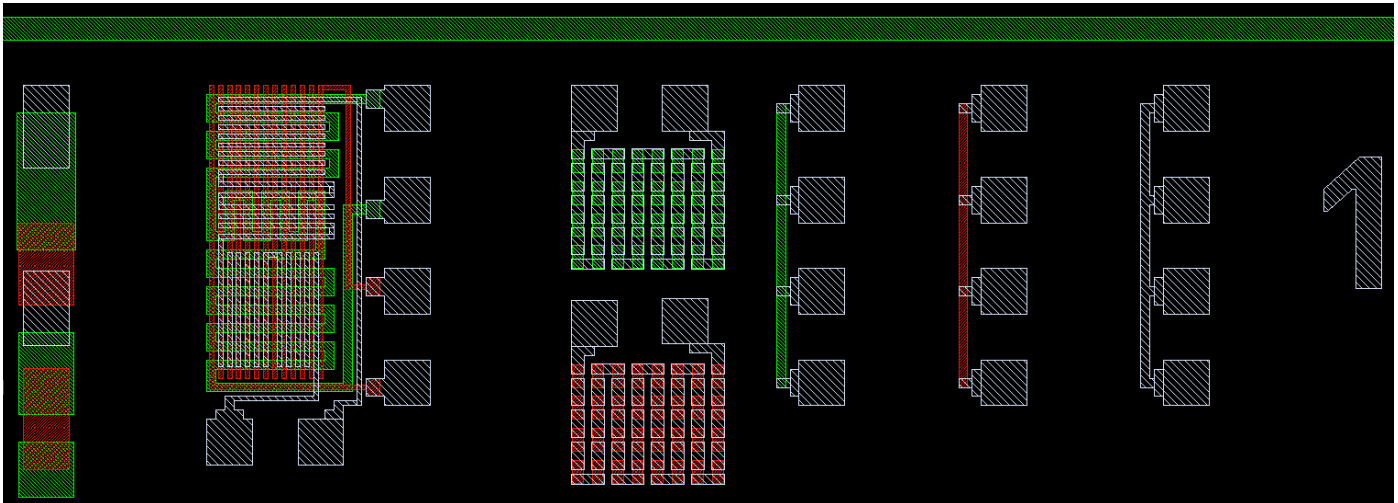
**Lignes 1 à 6 :**



**Ligne 1 : motifs d'alignement**



- Niveau 1 : DIFF
- Niveau 2 : POLY
- Niveau 3 : METAL
- Niveau 4 : FAR

**Ligne 1 :**

Motif test profilomètre, 2 chaînes de contacts, et R carrée (résistivité métal, poly et cristal dopé) : longueur du barreau :  $620\mu\text{m}$  – largeur  $20\mu\text{m}$ ;

Taille des plots de métal :  $100\mu\text{m} \times 100\mu\text{m}$

Numéros des niveaux de masque :

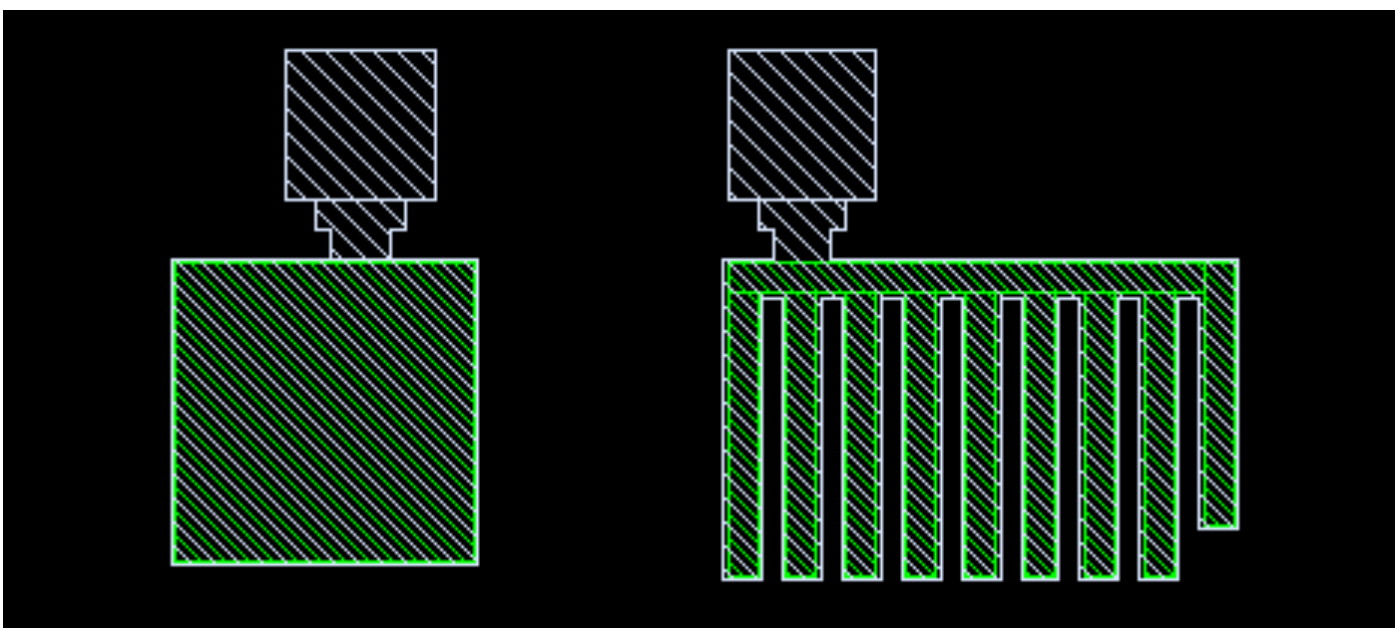
1 DIFFusion, 2 POLY(Silicium xCristallin), 3 METal (Aluminium), 4 gravure Face ARrière

**Ligne 2:**

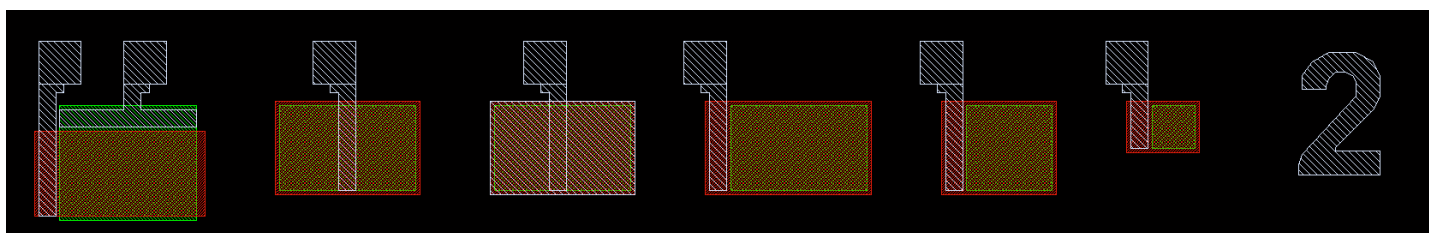
Diode  $200 \times 200\mu\text{m}$  de grande surface et petit périmètre ;

diode de grande surface et de grand périmètre :

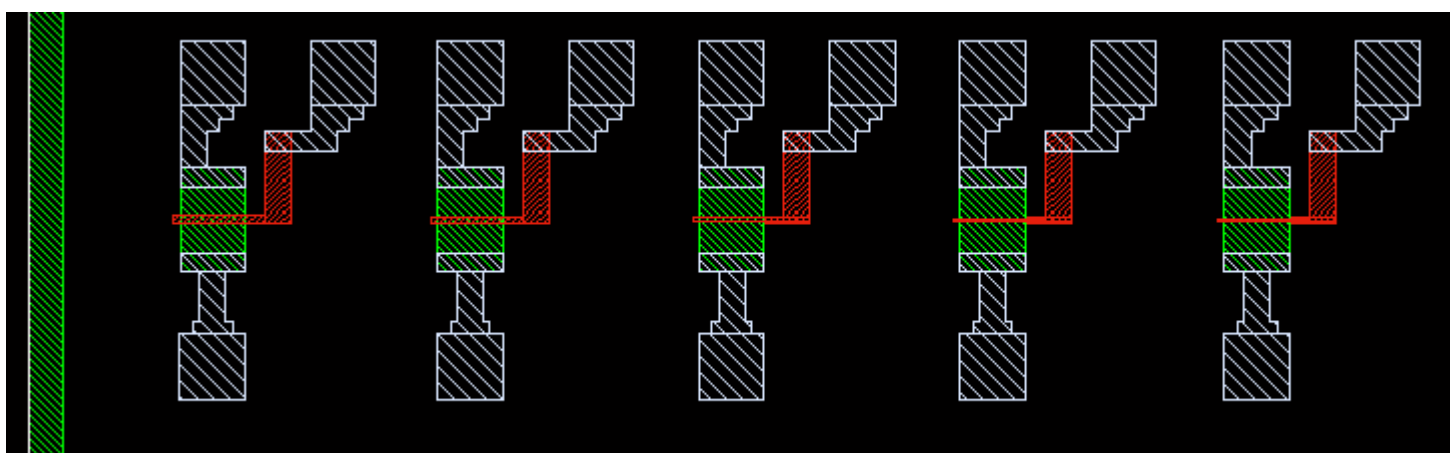
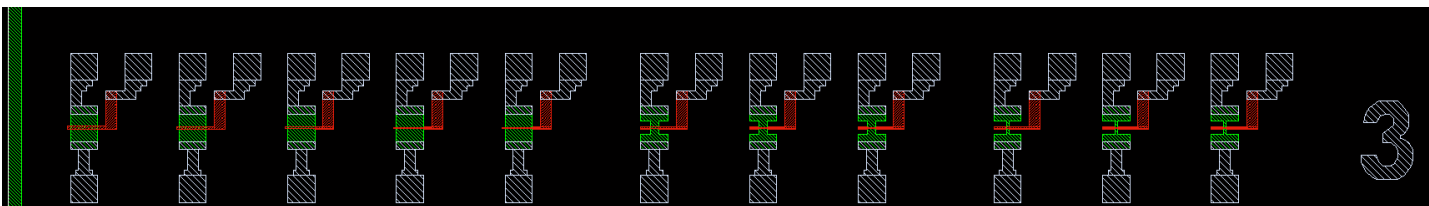
$340\mu\text{m} \times 20\mu\text{m}$  ;  $8 \times 190\mu\text{m} \times 20\mu\text{m}$  ;  $20\mu\text{m} \times 155\mu\text{m}$



Capacités MOS (4 de 320\*200µm, 200\*200µm et 100\*100µm)

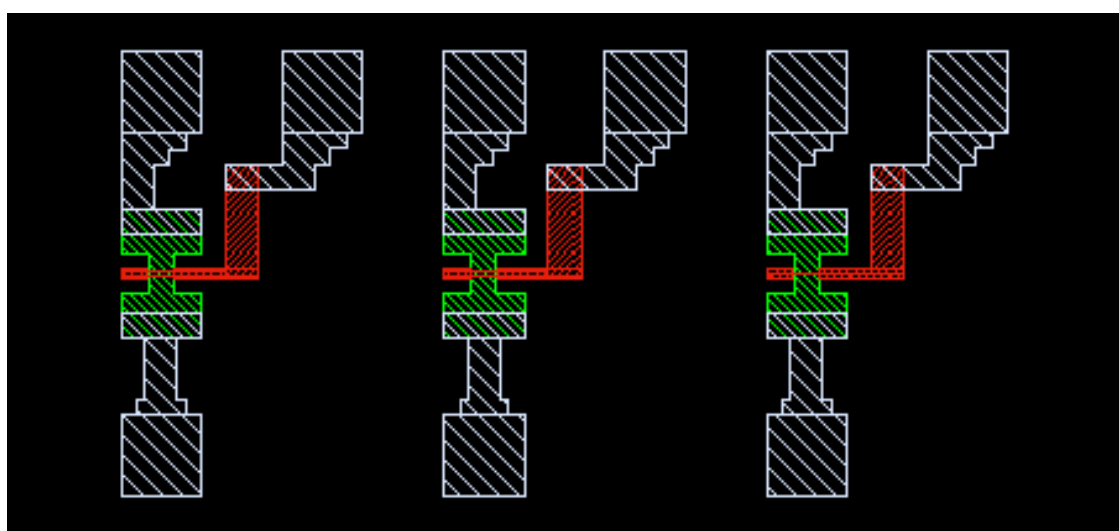


**Ligne 3 (Lignes 4, 5 et 6 identiques à 3) :**



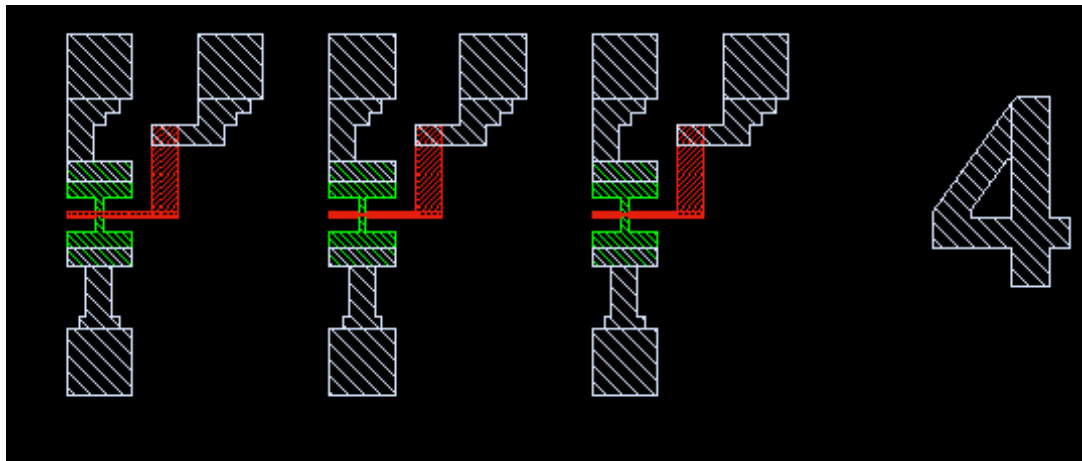
Transistors MOS

W=100µm, l= 12; 10; 6; 4; 2µm



Transistors MOS

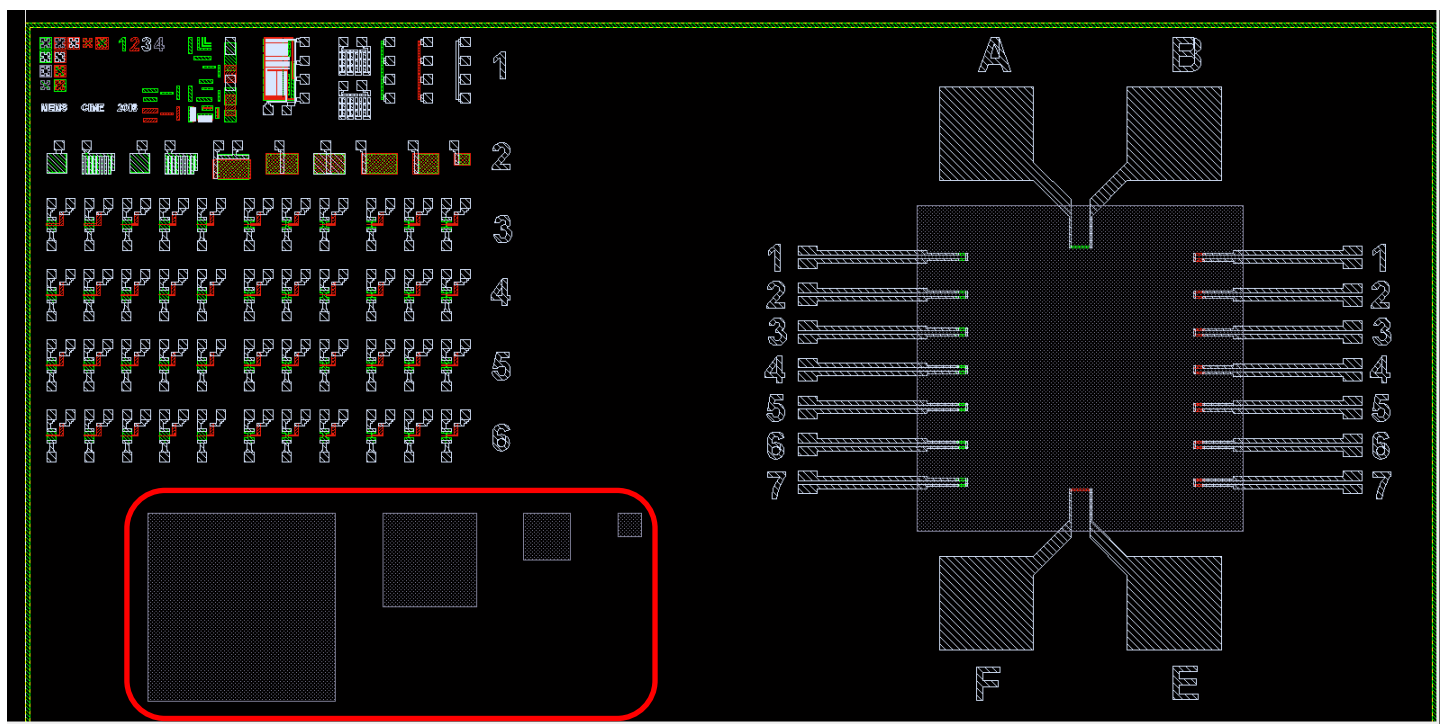
W=30µm, l=6; 4; 2µm



Transistor MOS

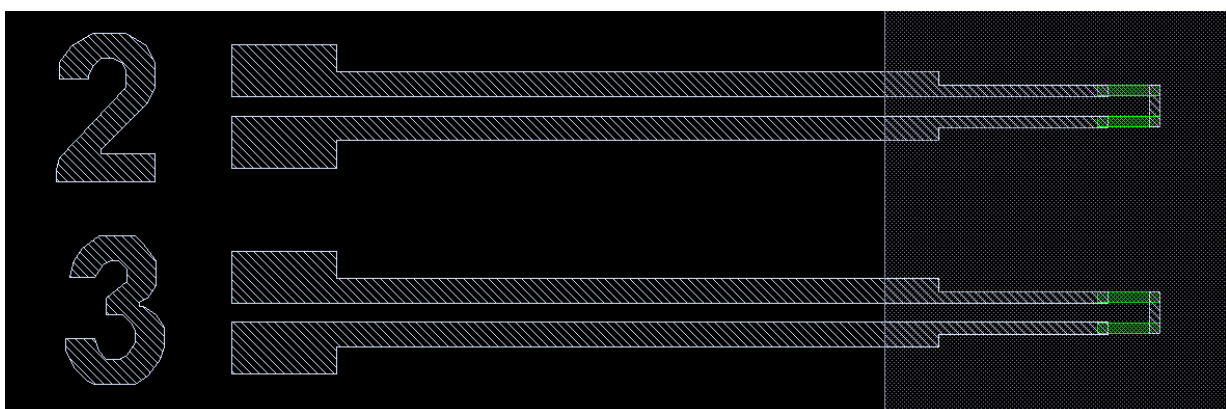
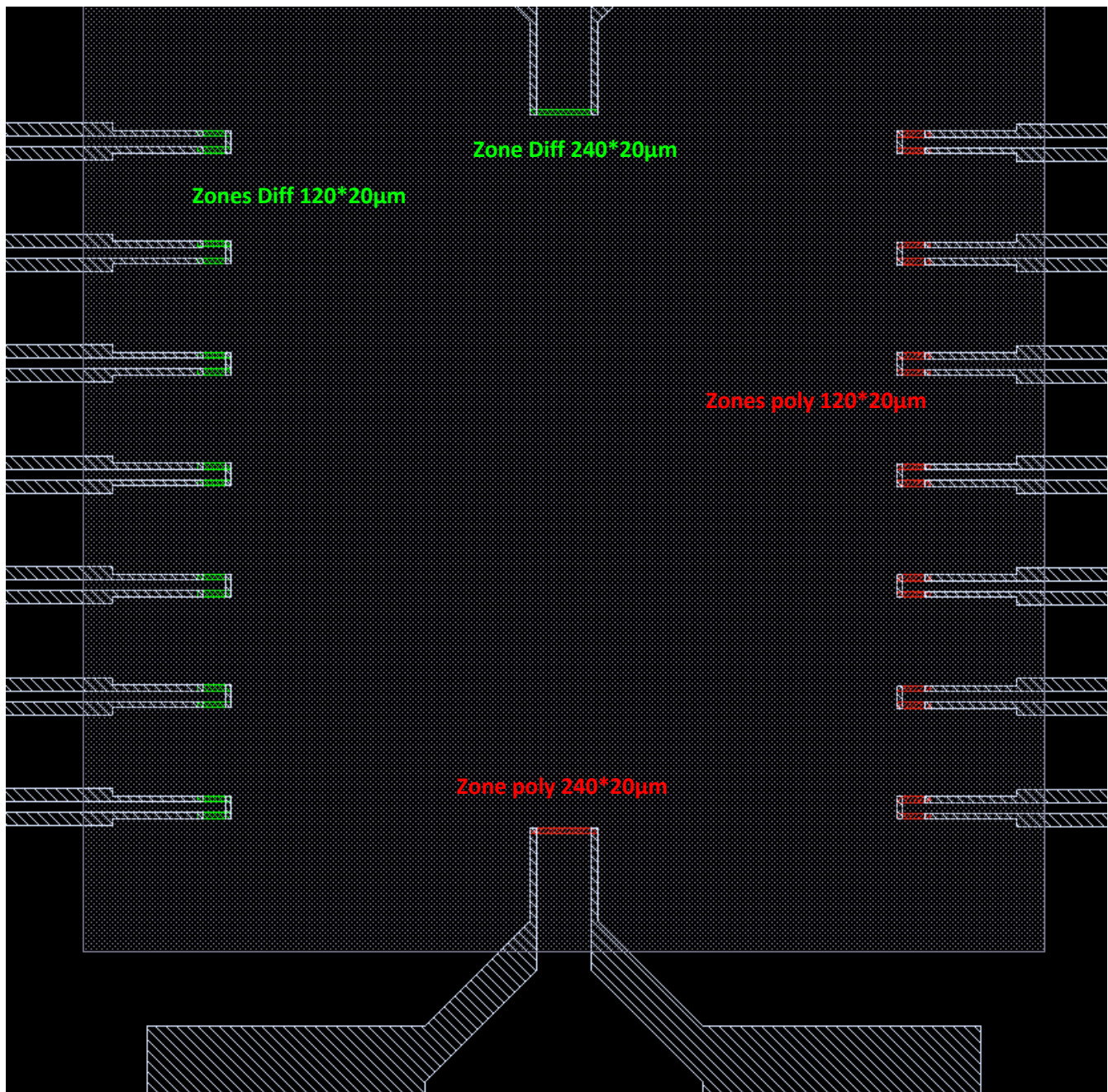
W=10μm, l=6; 4; 2μm

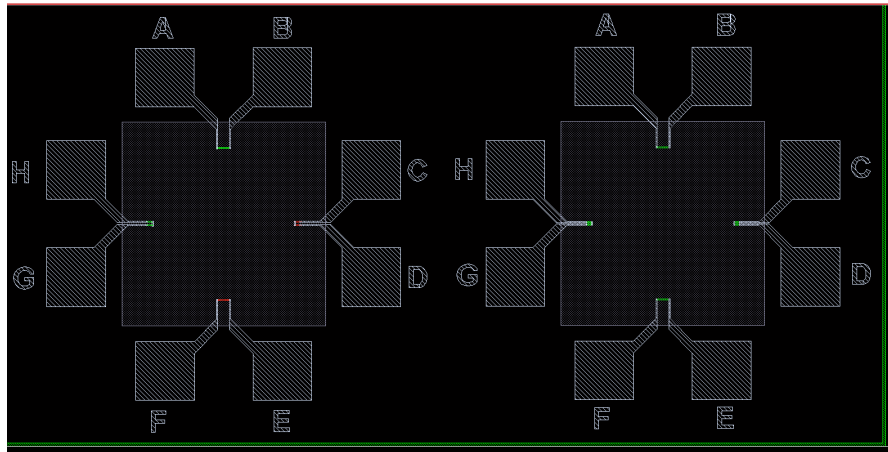
**Membranes :**



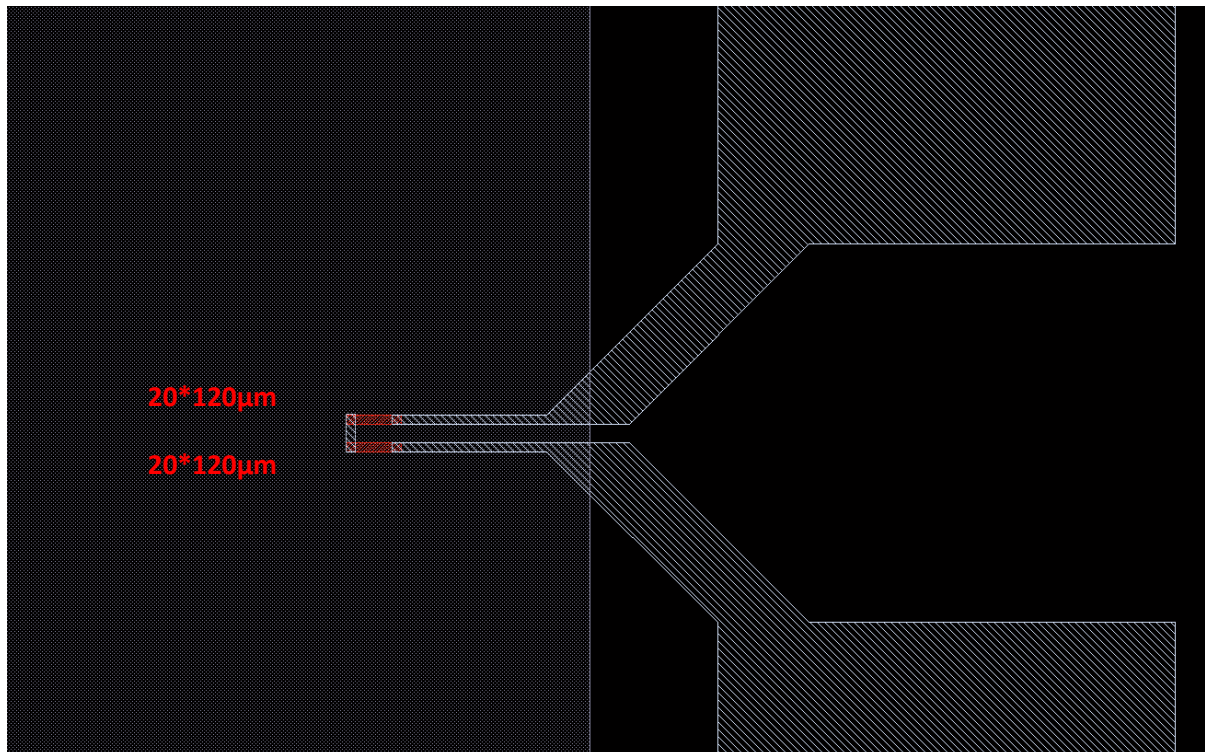
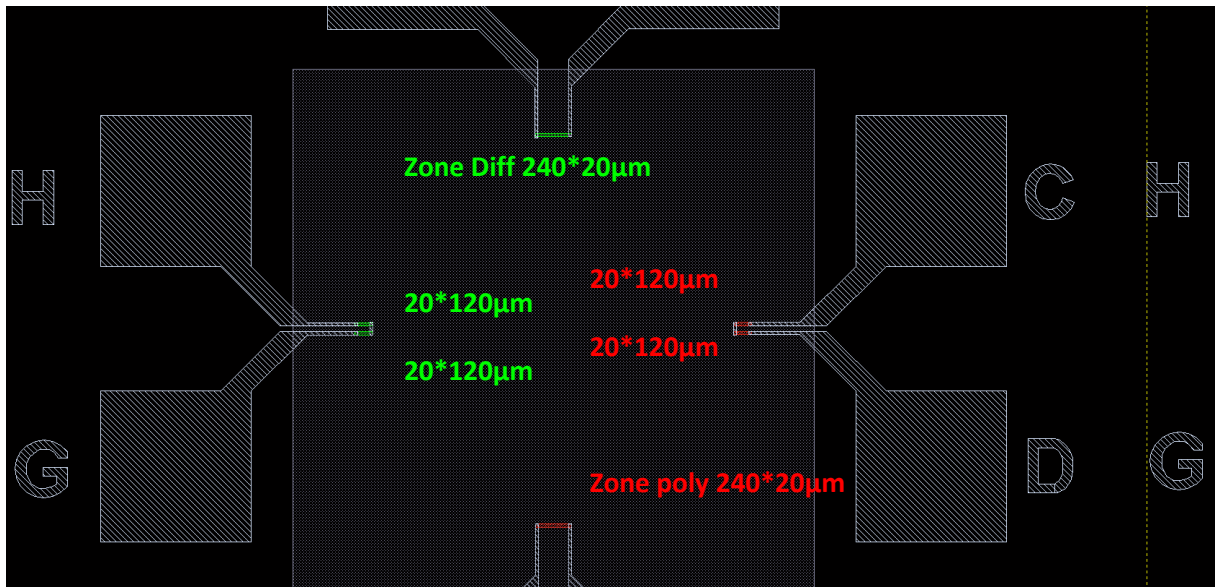
**Membranes 2000\*2000μm; 1000\*1000μm; 500\*500μm; 250\*250μm**

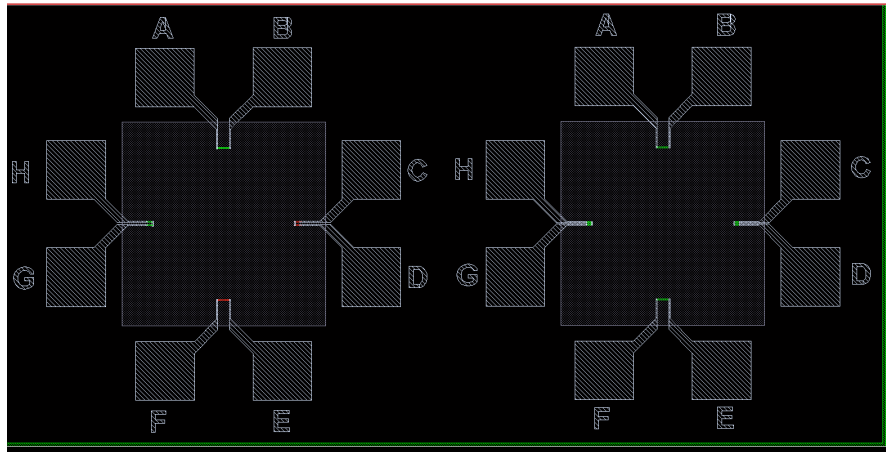
Jauges sur membrane carrée de 3466\*3466μm





Membrane de gauche :





Membrane de droite:

